



STB120N4LF6 STD120N4LF6

N-channel 40 V, 3.1 mΩ, 80 A DPAK, D²PAK
STripFET™ VI DeepGATE™ Power MOSFET

Features

| Order codes | V _{DSS} | R _{DS(on) max} | I _D |
|-------------|------------------|-------------------------|----------------|
| STB120N4LF6 | 40 V | 4.0 mΩ | 80 A |
| STD120N4LF6 | 40 V | 4.0 mΩ | 80 A |

- Logic level drive
- 100% avalanche tested

Application

- Switching applications
 - Automotive

Description

This product is a 40 V N-channel STripFET™ VI Power MOSFET based on the ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest RDS(on) in all packages.

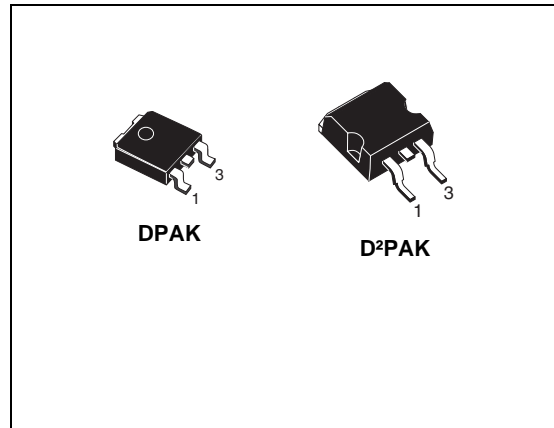


Figure 1. Internal schematic diagram

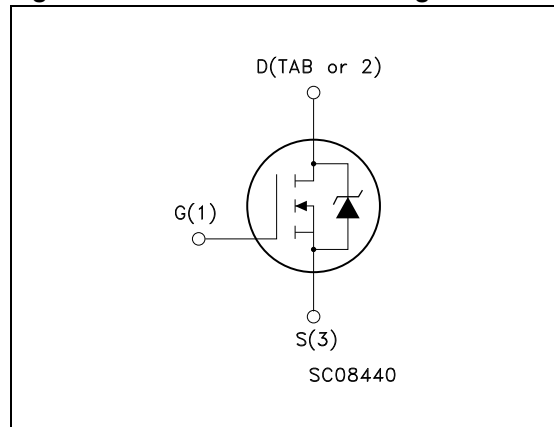


Table 1. Device summary

| Order codes | Marking | Packages | Packaging |
|-------------|----------|--------------------|---------------|
| STB120N4LF6 | 120N4LF6 | D ² PAK | Tape and reel |
| STD120N4LF6 | | DPAK | |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|------------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 40 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 80 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 80 | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 320 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 110 | W |
| T_{stg} | Storage temperature | -55 to 175 | $^\circ\text{C}$ |
| T_j | Operating junction temperature | | |

- Limited by wire bonding
- Pulse width limited by safe operating area

Table 3. Thermal resistance

| Symbol | Parameter | Value | | Unit |
|----------------|--|-------|--------------------|--------------------|
| | | DPAK | D ² PAK | |
| $R_{thj-case}$ | Thermal resistance junction-case max | 1.36 | | $^\circ\text{C/W}$ |
| $R_{thj-pcb}$ | Thermal resistance junction-pcb max ⁽¹⁾ | 50 | 35 | $^\circ\text{C/W}$ |

- When mounted on 1 inch² 2 oz. Cu board.

Table 4. Avalanche data

| Symbol | Parameter | Value | Unit |
|----------------|----------------------------------|-------|------|
| I_{AV} | Not-repetitive avalanche current | 40 | A |
| $E_{AS}^{(1)}$ | Single pulse avalanche energy | 394 | mJ |

- Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 40\text{ A}$, $V_{DD} = 25\text{ V}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. Static

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|-----------|--------------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown Voltage | $I_D = 250\ \mu\text{A}$, $V_{GS} = 0$ | 40 | - | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = 20\text{ V}$ $V_{DS} = 20\text{ V}$, $T_c = 125\text{ °C}$ | | - | 1 10 | μA μA |
| I_{GSS} | Gate body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20\text{ V}$ | | - | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$ | 1 | - | 3 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 5\text{ V}$, $I_D = 40\text{ A}$ | | 3.6 | 5.0 | $\text{m}\Omega$ |
| | | $V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$ | | 3.1 | 4.0 | $\text{m}\Omega$ |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min | Typ. | Max. | Unit |
|-----------|------------------------------|--|-----|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$ | - | 4300 | - | pF |
| C_{oss} | Output capacitance | | | 650 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 375 | | pF |
| Q_g | Total gate charge | $V_{DD} = 20\text{ V}$, $I_D = 80\text{ A}$ | - | 80 | - | nC |
| Q_{gs} | Gate-source charge | $V_{GS} = 10\text{ V}$ | | 15 | | nC |
| Q_{gd} | Gate-drain charge | (see Figure 14) | | 15 | | nC |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz}$ open drain | | 1.35 | | Ω |

Table 7. Switching on/off (inductive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|----------------------------------|--|------|-----------|------|----------|
| $t_{d(on)}$ t_r | Turn-on delay time Rise time | $V_{DD} = 20\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>Figure 15</i> | - | 15 95 | - | ns ns |
| $t_{d(off)}$ t_f | Turn-off delay time Fall time | | - | 125 45 | - | ns ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|-----------------|-----------|---------------|
| I_{SD} $I_{SDM}^{(1)}$ | Source-drain current Source-drain current (pulsed) | | - | | 80 320 | A A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 40\text{ A}$, $V_{GS} = 0$ | - | | 1.1 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 32\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ <i>Figure 17</i> | - | 50 85 3.5 | | ns nC A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

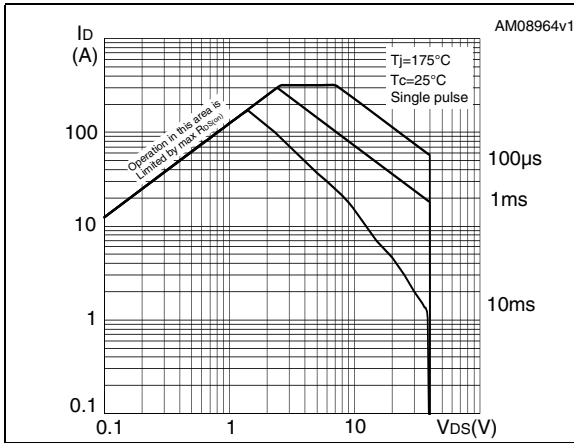


Figure 3. Thermal impedance

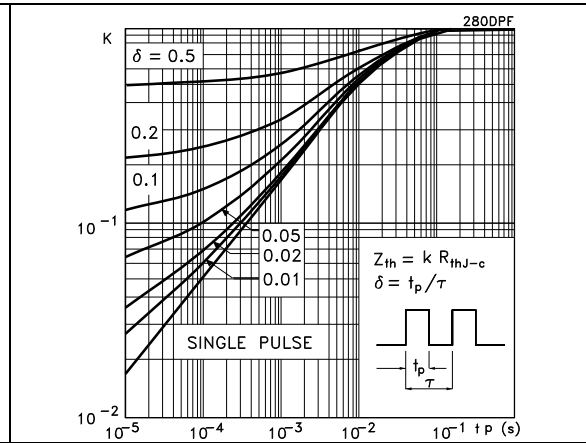


Figure 4. Output characteristics

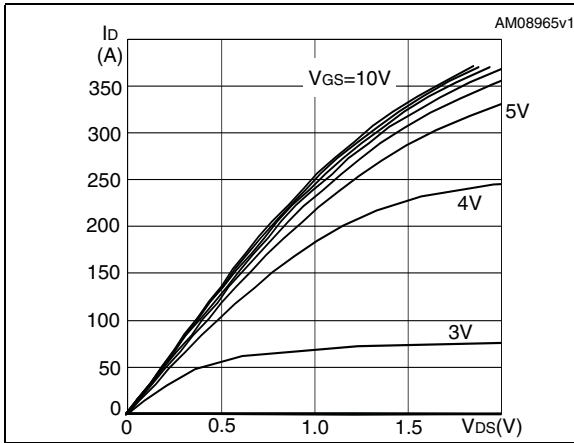


Figure 5. Transfer characteristics

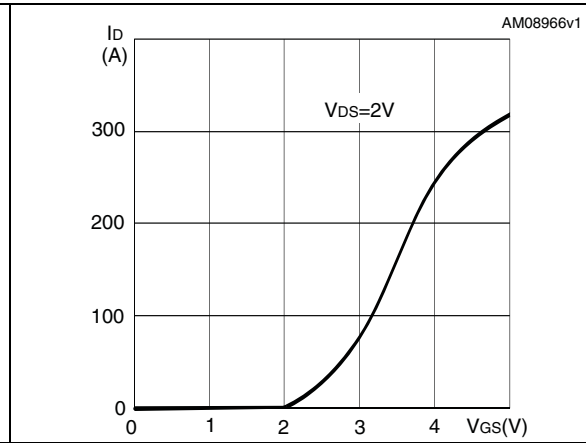


Figure 6. Normalized $B_{V_{DSS}}$ vs temperature

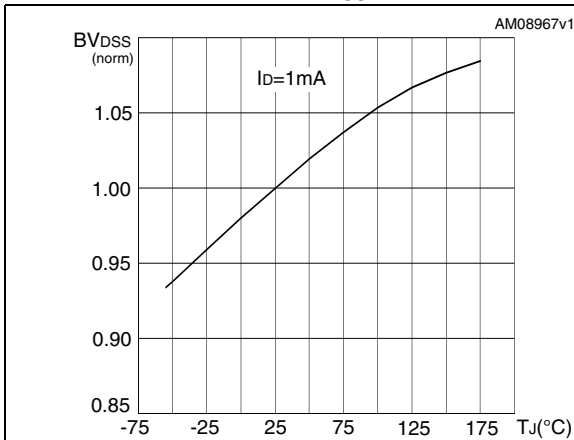


Figure 7. Static drain-source on resistance

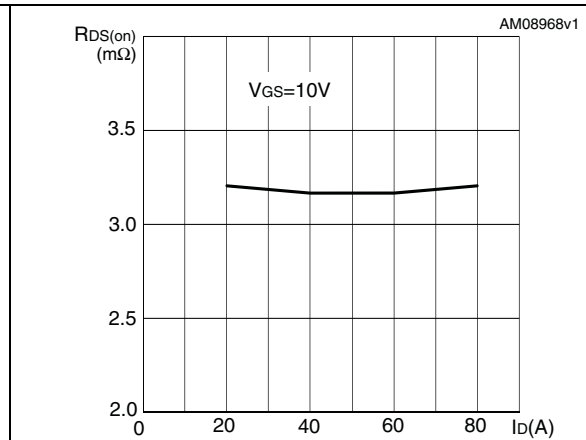


Figure 8. Gate charge vs gate-source voltage **Figure 9. Capacitance variations**

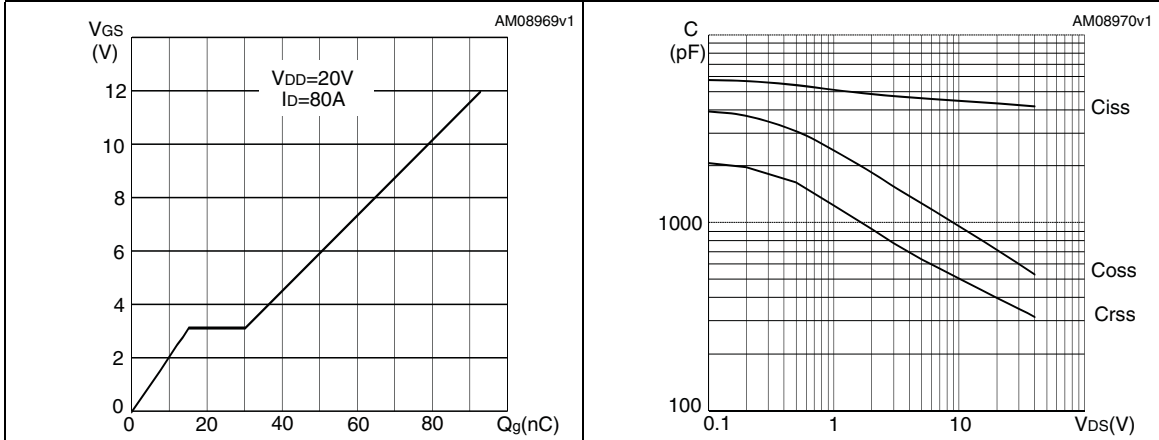


Figure 10. Normalized gate threshold voltage vs temperature **Figure 11. Normalized on resistance vs temperature**

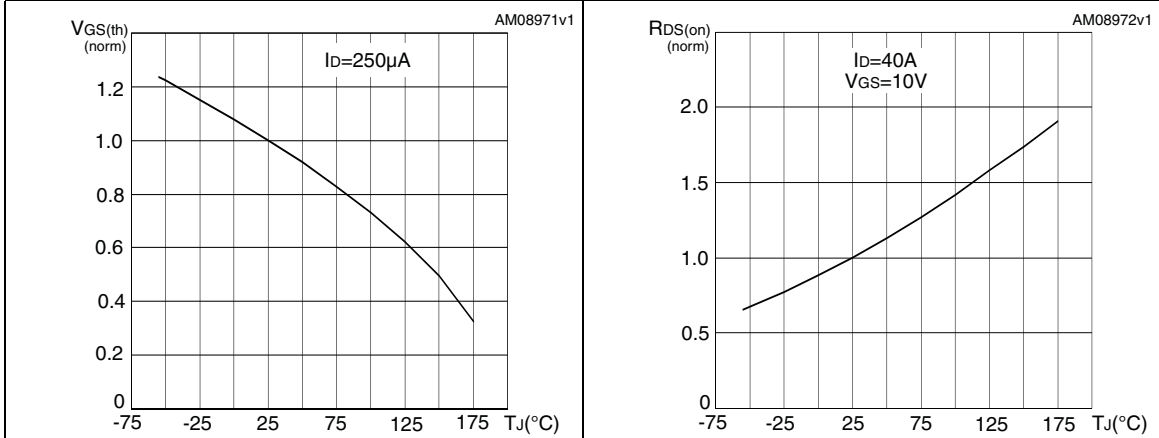
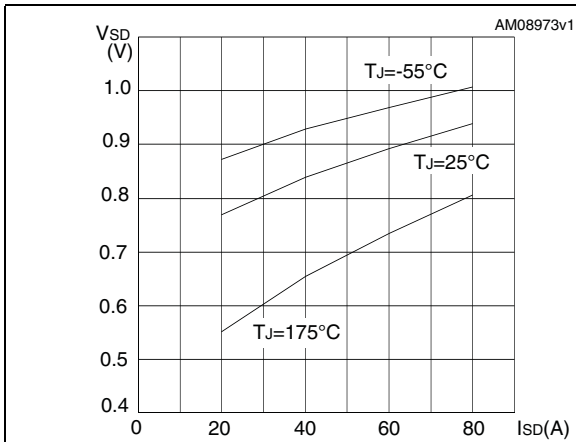


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

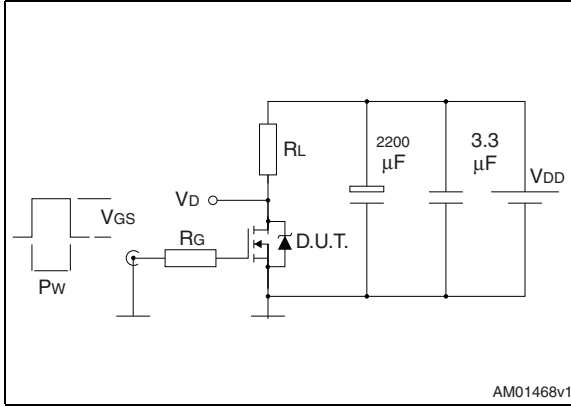


Figure 14. Gate charge test circuit

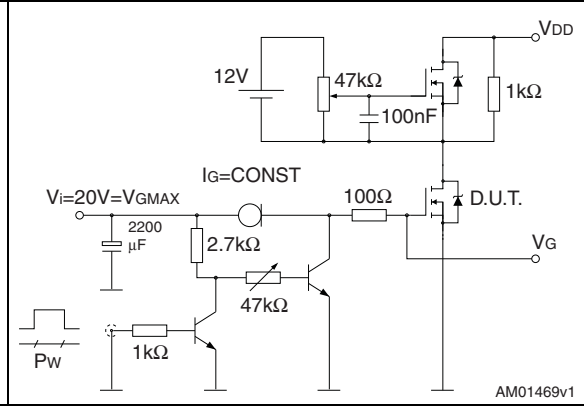


Figure 15. Test circuit for inductive load switching and diode recovery times

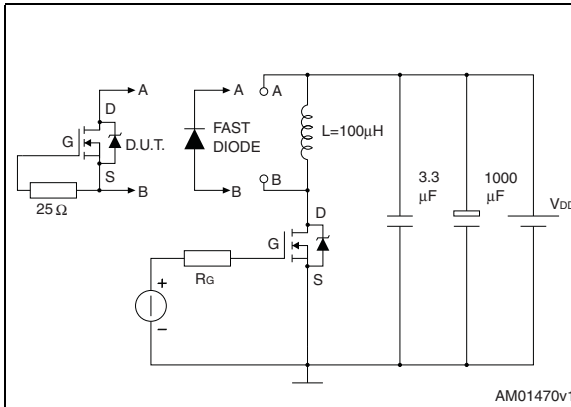


Figure 16. Unclamped inductive load test circuit

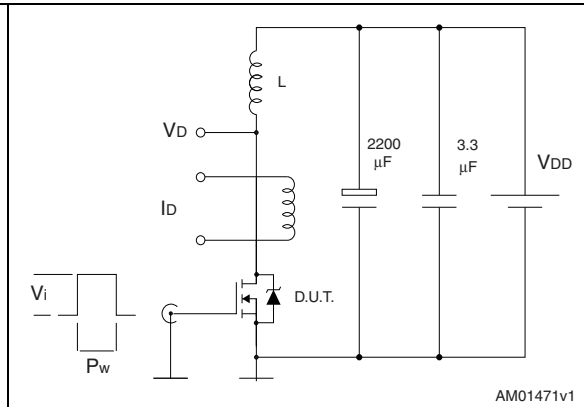


Figure 17. Unclamped inductive waveform

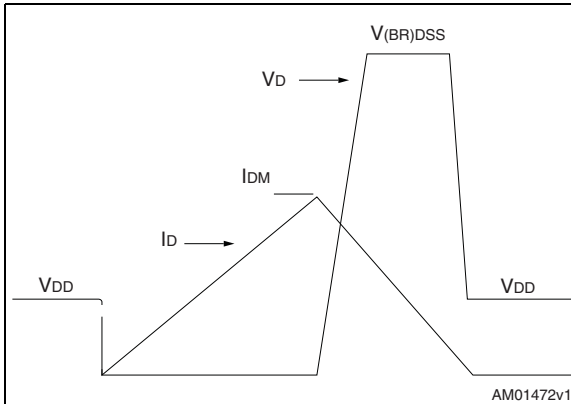
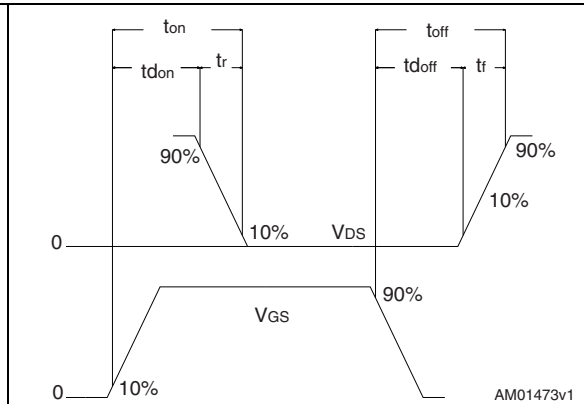


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and products status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 4.40 | | 4.60 |
| A1 | 0.03 | | 0.23 |
| b | 0.70 | | 0.93 |
| b2 | 1.14 | | 1.70 |
| c | 0.45 | | 0.60 |
| c2 | 1.23 | | 1.36 |
| D | 8.95 | | 9.35 |
| D1 | 7.50 | | |
| E | 10 | | 10.40 |
| E1 | 8.50 | | |
| e | | 2.54 | |
| e1 | 4.88 | | 5.28 |
| H | 15 | | 15.85 |
| J1 | 2.49 | | 2.69 |
| L | 2.29 | | 2.79 |
| L1 | 1.27 | | 1.40 |
| L2 | 1.30 | | 1.75 |
| R | | 0.4 | |
| V2 | 0° | | 8° |

Figure 19. D²PAK (TO-263) drawing

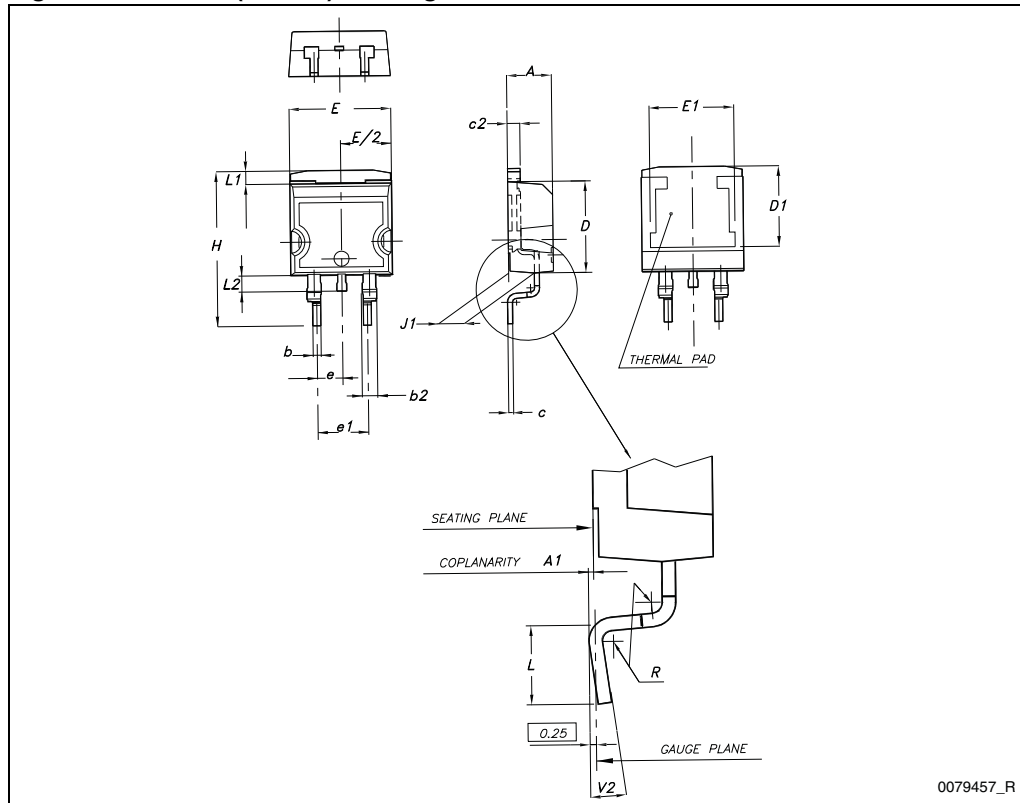
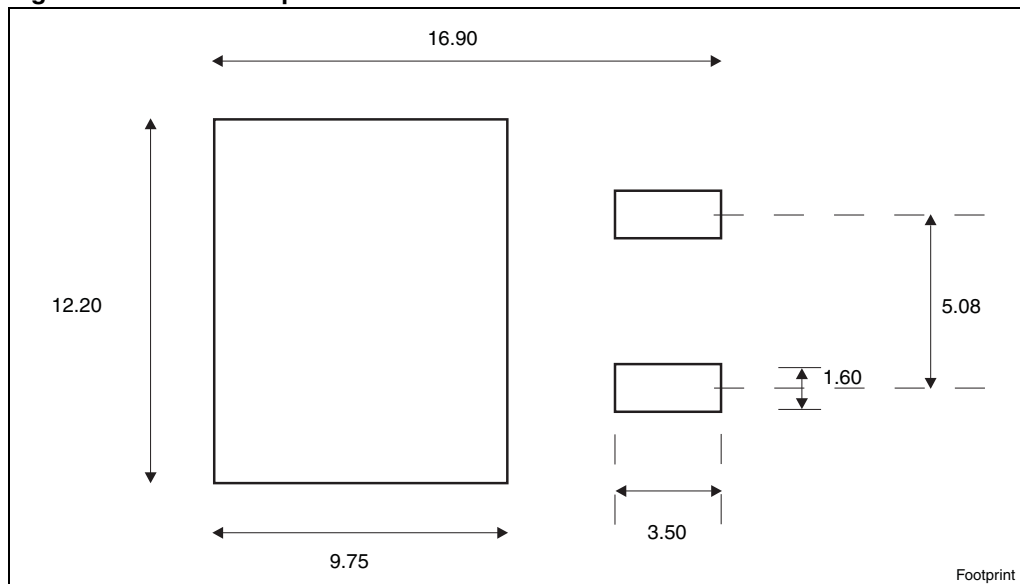


Figure 20. D²PAK footprint^(a)



a. All dimension are in millimeters

Table 10. DPAK (TO-252) mechanical data

| Dim. | mm | | |
|------|------|------|-------|
| | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 |
| A1 | 0.90 | | 1.10 |
| A2 | 0.03 | | 0.23 |
| b | 0.64 | | 0.90 |
| b4 | 5.20 | | 5.40 |
| c | 0.45 | | 0.60 |
| c2 | 0.48 | | 0.60 |
| D | 6.00 | | 6.20 |
| D1 | | 5.10 | |
| E | 6.40 | | 6.60 |
| E1 | | 4.70 | |
| e | | 2.28 | |
| e1 | 4.40 | | 4.60 |
| H | 9.35 | | 10.10 |
| L | 1 | | |
| L1 | | 2.80 | |
| L2 | | 0.80 | |
| L4 | 0.60 | | 1 |
| R | | 0.20 | |
| V2 | 0° | | 8° |

Figure 21. DPAK (TO-252) drawing

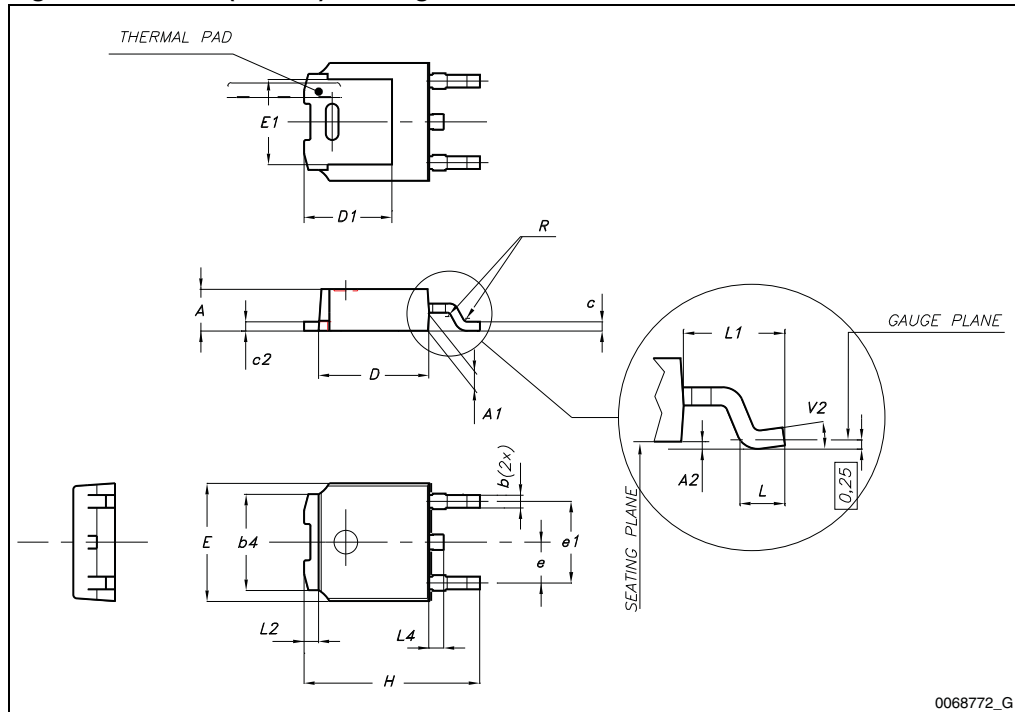
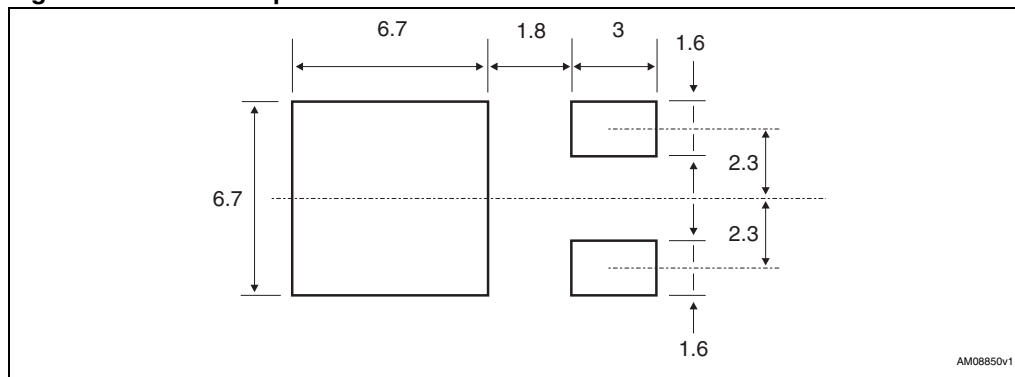


Figure 22. DPAK footprint^(b)



b. All dimension are in millimeters

5 Packaging mechanical data

Table 11. D²PAK (TO-263) tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|------|----------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 10.5 | 10.7 | A | | 330 |
| B0 | 15.7 | 15.9 | B | 1.5 | |
| D | 1.5 | 1.6 | C | 12.8 | 13.2 |
| D1 | 1.59 | 1.61 | D | 20.2 | |
| E | 1.65 | 1.85 | G | 24.4 | 26.4 |
| F | 11.4 | 11.6 | N | 100 | |
| K0 | 4.8 | 5.0 | T | | 30.4 |
| P0 | 3.9 | 4.1 | | | |
| P1 | 11.9 | 12.1 | | Base qty | 1000 |
| P2 | 1.9 | 2.1 | | Bulk qty | 1000 |
| R | 50 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 23.7 | 24.3 | | | |

Table 12. DPAK (TO-252) tape and reel mechanical data

| Tape | | | Reel | | |
|------|------|------|-----------|------|------|
| Dim. | mm | | Dim. | mm | |
| | Min. | Max. | | Min. | Max. |
| A0 | 6.8 | 7 | A | | 330 |
| B0 | 10.4 | 10.6 | B | 1.5 | |
| B1 | | 12.1 | C | 12.8 | 13.2 |
| D | 1.5 | 1.6 | D | 20.2 | |
| D1 | 1.5 | | G | 16.4 | 18.4 |
| E | 1.65 | 1.85 | N | 50 | |
| F | 7.4 | 7.6 | T | | 22.4 |
| K0 | 2.55 | 2.75 | | | |
| P0 | 3.9 | 4.1 | Base qty. | | 2500 |
| P1 | 7.9 | 8.1 | Bulk qty. | | 2500 |
| P2 | 1.9 | 2.1 | | | |
| R | 40 | | | | |
| T | 0.25 | 0.35 | | | |
| W | 15.7 | 16.3 | | | |

Figure 23. Tape for D²PAK(TO-263) and DPAK (TO-252)

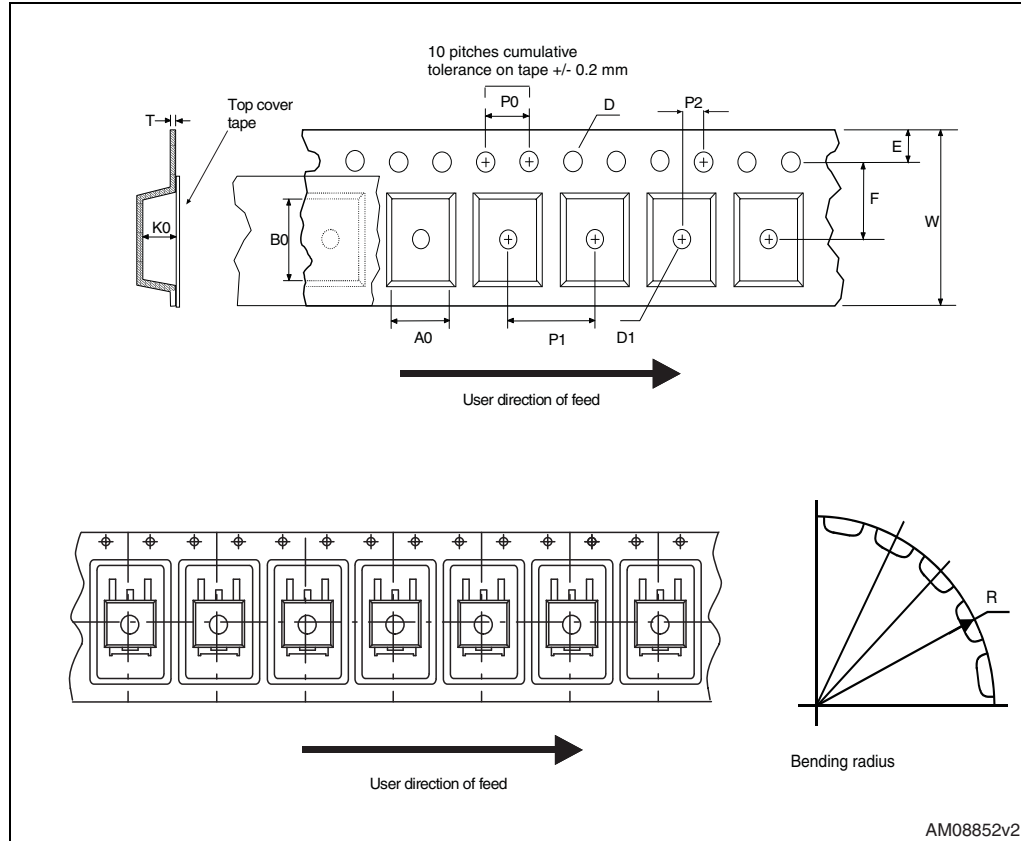
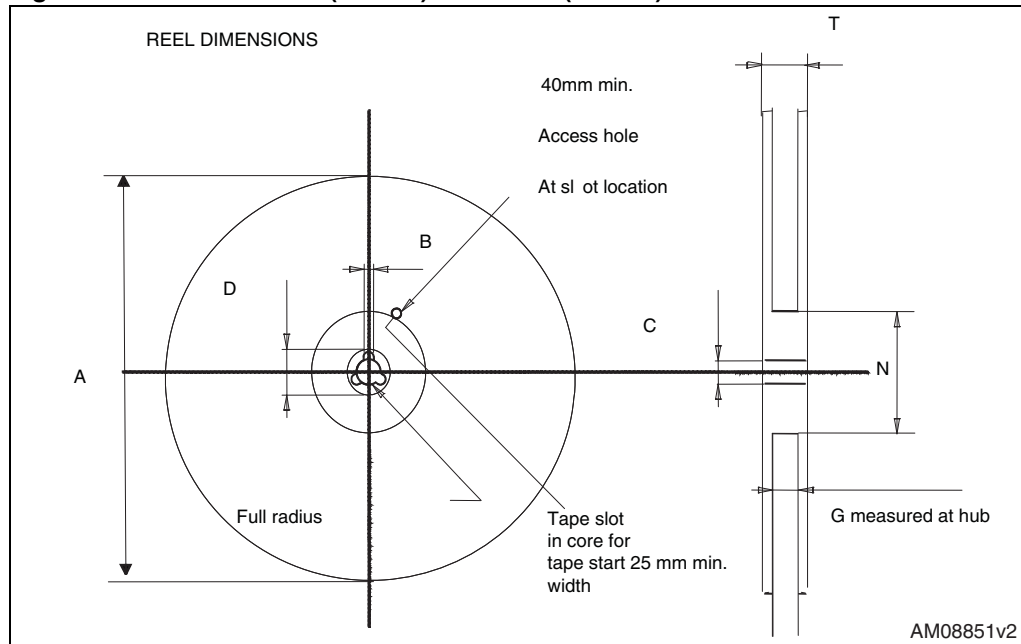


Figure 24. Reel for D²PAK(TO-263) and DPAK (TO-252)



6 Revision history

Table 13. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 14-Dec-2009 | 1 | First release |
| 23-Feb-2011 | 2 | Document status promoted from preliminary data to datasheet. |

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